

Vishay Siliconix

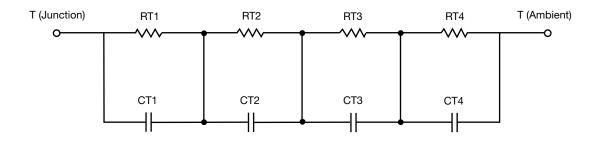
R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

R-C THERMAL MODEL FOR TANK CONFIGURATION



-C VALUES FOR TANK CONFIGURATION						
THERMAL RESISTANCE (°C/W)						
Junction to	Ambient	Case	Foot			
RT1	2.8636	594.5919m	N/A			
RT2	7.8730	790.2397m	N/A			
RT3	19.8213	977.2405m	N/A			
RT4	19.4126	818.2747m	N/A			
	THERMAL CAPAC	ITANCE (Joules/°C)				
Junction to	Ambient	Case	Foot			
CT1	6.4479m	7.5018m	N/A			
CT2	87.7096m	14.1405m	N/A			
CT3	3.9296	78.3912m	N/A			
CT4	923.1114m	826.3608u	N/A			

Note

N/A indicates not applicable

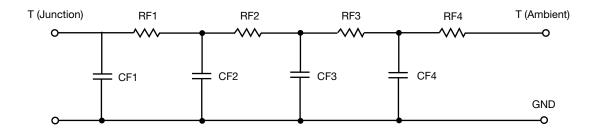
This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

Document Number: 67914 www.vishay.com Revision: 13-Apr-11

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R-C THERMAL MODEL FOR FILTER CONFIGURATION



R-C VALUES FOR FILTER CONFIGURATION THERMAL RESISTANCE (°C/W)					
RF1	3.2977	1.3125	N/A		
RF2	8.2830	1.4247	N/A		
RF3	21.5644	1.7673m	N/A		
RF4	16.6061	475.4737m	N/A		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	6.7991m	800.4575u	N/A		
CF2	64.5697m	10.2569m	N/A		
CF3	576.6701m	66.7624u	N/A		
CF4	2.7192	335.2730m	N/A		

Note

N/A indicates not applicable





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